

Philippe Venngus

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#	Paper	IF	Citations
203	Stress control in GaN grown on silicon (111) by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2001 , 79, 3230-3232	3.4	227
202	Physical characterization of molybdenum oxycarbide catalyst; TEM, XRD and XPS. <i>Catalysis Today</i> , 1995 , 23, 251-267	5.3	174
201	Reduction mechanisms for defect densities in GaN using one- or two-step epitaxial lateral overgrowth methods. <i>Journal of Applied Physics</i> , 2000 , 87, 4175-4181	2.5	165
200	Influence of in situ sapphire surface preparation and carrier gas on the growth mode of GaN in MOVPE. <i>Journal of Crystal Growth</i> , 1998 , 187, 167-177	1.6	117
199	Growth of high-quality GaN by low-pressure metal-organic vapour phase epitaxy (LP-MOVPE) from 3D islands and lateral overgrowth. <i>Journal of Crystal Growth</i> , 1999 , 205, 245-252	1.6	106
198	Defect characterization in ZnO layers grown by plasma-enhanced molecular-beam epitaxy on (0001) sapphire substrates. <i>Applied Physics Letters</i> , 2001 , 79, 194-196	3.4	102
197	Pyramidal defects in metalorganic vapor phase epitaxial Mg doped GaN. <i>Applied Physics Letters</i> , 2000 , 77, 880-882	3.4	101
196	Luminescence and reflectivity studies of undoped, n- and p-doped GaN on (0001) sapphire. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 50, 97-104	3.1	97
195	Cathodoluminescence spectroscopy of epitaxial-lateral-overgrown nonpolar (11-20) and semipolar (11-22) GaN in relation to microstructural characterization. <i>Journal of Applied Physics</i> , 2007 , 101, 113101	2.5	95
194	Optimisation of AlN and GaN growth by metalorganic vapour-phase epitaxy (MOVPE) on Si (1 1 1). <i>Journal of Crystal Growth</i> , 2000 , 217, 13-25	1.6	87
193	Molecular-beam epitaxy of gallium nitride on (0001) sapphire substrates using ammonia. <i>Journal of Applied Physics</i> , 1998 , 83, 1379-1383	2.5	83
192	Growth of high quality crack-free AlGaIn films on GaN templates using plastic relaxation through buried cracks. <i>Journal of Applied Physics</i> , 2003 , 94, 6499-6507	2.5	80
191	The effect of the Si/N treatment of a nitridated sapphire surface on the growth mode of GaN in low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 1998 , 73, 1278-1280	3.4	69
190	Polarity Control in Group-III Nitrides beyond Pragmatism. <i>Physical Review Applied</i> , 2016 , 5,	4.3	68
189	Microstructural Characterization of Semipolar GaN Templates and Epitaxial-Lateral-Overgrown Films Deposited on M-Plane Sapphire by Metalorganic Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 4089-4095	1.4	68
188	Atomic structure of pyramidal defects in Mg-doped GaN. <i>Physical Review B</i> , 2003 , 68,	3.3	66
187	Polarity inversion of GaN(0001) by a high Mg doping. <i>Journal of Crystal Growth</i> , 2004 , 269, 249-256	1.6	61

186	Mg-enhanced lateral overgrowth of GaN on patterned GaN/sapphire substrate by selective Metal Organic Vapor Phase Epitaxy. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1998 , 3, 1		57
185	Microstructure of GaN epitaxial films at different stages of the growth process on sapphire (0 0 0 1). <i>Journal of Crystal Growth</i> , 1997 , 173, 249-259	1.6	56
184	Interface structure and anisotropic strain relaxation of nonpolar wurtzite (112 $\bar{0}$) and (101 $\bar{0}$) orientations: ZnO epilayers grown on sapphire. <i>Journal of Applied Physics</i> , 2008 , 104, 073535	2.5	55
183	Defect reduction method in (11-22) semipolar GaN grown on patterned sapphire substrate by MOCVD: Toward heteroepitaxial semipolar GaN free of basal stacking faults. <i>Journal of Crystal Growth</i> , 2014 , 404, 177-183	1.6	54
182	Epitaxial relationships between GaN and Al ₂ O ₃ (0001) substrates. <i>Applied Physics Letters</i> , 1997 , 70, 643-645	2.4	54
181	Non-polar a-plane ZnMgO/ZnO quantum wells grown by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2008 , 23, 035005	1.8	54
180	Study of open-core dislocations in GaN films on (0001) sapphire. <i>Applied Physics Letters</i> , 1997 , 70, 2434-2436	2.4	53
179	The critical role of growth temperature on the structural and electrical properties of AlGaIn/GaN high electron mobility transistor heterostructures grown on Si(111). <i>Journal of Applied Physics</i> , 2009 , 105, 033701	2.5	47
178	Indium incorporation dynamics into AlInN ternary alloys for laser structures lattice matched to GaN. <i>Applied Physics Letters</i> , 2008 , 93, 081116	3.4	47
177	Catalytic unzipping of carbon nanotubes to few-layer graphene sheets under microwaves irradiation. <i>Applied Catalysis A: General</i> , 2009 , 371, 22-30	5.1	46
176	Interfacial structure and defect analysis of nonpolar ZnO films grown on R-plane sapphire by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2008 , 103, 083525	2.5	44
175	On the polarity of GaN micro- and nanowires epitaxially grown on sapphire (0001) and Si(111) substrates by metal organic vapor phase epitaxy and ammonia-molecular beam epitaxy. <i>Applied Physics Letters</i> , 2011 , 98, 011914	3.4	42
174	Stacking faults blocking process in (11 $\bar{0}$ 2) semipolar GaN growth on sapphire using asymmetric lateral epitaxy. <i>Journal of Crystal Growth</i> , 2010 , 312, 2625-2630	1.6	41
173	Growth modes and microstructures of ZnO layers deposited by plasma-assisted molecular-beam epitaxy on (0001) sapphire. <i>Journal of Applied Physics</i> , 2001 , 90, 5115-5119	2.5	41
172	GaN epitaxial growth on sapphire (0 0 0 1): the role of the substrate nitridation. <i>Journal of Crystal Growth</i> , 1997 , 178, 220-228	1.6	40
171	Growth of non-polar ZnO/(Zn,Mg)O quantum well structures on R-sapphire by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 366-369	1.6	40
170	Dual-polarity GaN micropillars grown by metalorganic vapour phase epitaxy: Cross-correlation between structural and optical properties. <i>Journal of Applied Physics</i> , 2014 , 115, 153504	2.5	39
169	Crack-Free Thick GaN Layers on Silicon (111) by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 2001 , 188, 531-535		39

168	A Two-Step Method for Epitaxial Lateral Overgrowth of GaN. <i>Physica Status Solidi A</i> , 1999 , 176, 567-571		39
167	GaN/GaN multiple-quantum-well light-emitting diodes grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1999 , 74, 3616-3618	3-4	39
166	Strain-compensated (Ga,In)N/(Al,Ga)N/GaN multiple quantum wells for improved yellow/amber light emission. <i>Applied Physics Letters</i> , 2015 , 106, 142101	3-4	38
165	Defect reduction methods for III-nitride heteroepitaxial films grown along nonpolar and semipolar orientations. <i>Semiconductor Science and Technology</i> , 2012 , 27, 024004	1.8	38
164	Structural changes in metastable epitaxial Co/Mn superlattices. <i>Physical Review B</i> , 1994 , 49, 8561-8573	3-3	38
163	Reduction of stacking faults in (11 $\bar{1}$ 0) and (11 $\bar{1}$ 2) GaN films by ELO techniques and benefit on GaN wells emission. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 282-289	1.6	37
162	Epitaxial lateral overgrowth of GaN on Si (111). <i>Journal of Applied Physics</i> , 2003 , 93, 182-185	2.5	37
161	Transmission electron microscopy study of the nitridation of the (0001) sapphire surface. <i>Applied Physics Letters</i> , 1999 , 75, 4115-4117	3-4	37
160	Strong decrease of the activation energy as a function of Al content in FeAl _x alloys (x \geq 30 at.%) deduced from kinetic measurements of ordering. <i>Acta Metallurgica Et Materialia</i> , 1990 , 38, 2199-2213		36
159	Anisotropic morphology of nonpolar a-plane GaN quantum dots and quantum wells. <i>Journal of Applied Physics</i> , 2007 , 102, 074304	2.5	35
158	Control of the polarity of GaN films using an Mg adsorption layer. <i>Journal of Crystal Growth</i> , 2003 , 251, 460-464	1.6	35
157	Structural and optical properties of lattice-matched ZnBeSe layers grown by molecular-beam epitaxy onto GaAs substrates. <i>Applied Physics Letters</i> , 1997 , 70, 3564-3566	3-4	34
156	Study of the epitaxial relationships between III-nitrides and M-plane sapphire. <i>Journal of Applied Physics</i> , 2010 , 108, 113521	2.5	33
155	Influence of high Mg doping on the microstructural and optoelectronic properties of GaN. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 93, 224-228	3-1	33
154	Band-edge photoluminescence and reflectivity of nonpolar (11 $\bar{1}$ 0) and semipolar (11 $\bar{1}$ 2) GaN formed by epitaxial lateral overgrowth on sapphire. <i>Physical Review B</i> , 2008 , 77,	3-3	32
153	Structural and electronic properties of ZnMgO/ZnO quantum wells. <i>Superlattices and Microstructures</i> , 2005 , 38, 455-463	2.8	32
152	Dislocation densities reduction in MBE-grown AlN thin films by high-temperature annealing. <i>Journal of Crystal Growth</i> , 2017 , 461, 10-15	1.6	30
151	In situ imaging of threading dislocation terminations at the surface of GaN(0001) epitaxially grown on Si(111). <i>Physical Review B</i> , 2000 , 61, 7618-7621	3-3	30

150	Imaging and counting threading dislocations in c-oriented epitaxial GaN layers. <i>Semiconductor Science and Technology</i> , 2013 , 28, 035006	1.8	29
149	Growth of Co/Ru strained superlattices. <i>Journal of Magnetism and Magnetic Materials</i> , 1992 , 104-107, 1873-1875	2.8	29
148	Effects of capping on GaN quantum dots deposited on Al _{0.5} Ga _{0.5} N by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2009 , 94, 143105	3.4	28
147	Relaxation mechanisms in metal-organic vapor phase epitaxy grown Al-rich (Al,Ga) _x N/GaN heterostructures. <i>Journal of Applied Physics</i> , 2005 , 97, 024912	2.5	28
146	Structural Defects and Relation with Optoelectronic Properties in Highly Mg-Doped GaN. <i>Physica Status Solidi A</i> , 2002 , 192, 394-400		28
145	Growth and characterization of A-plane ZnO and ZnCoO based heterostructures. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 88, 65-69	2.6	27
144	Characterization of structural defects in (11 $\bar{2}$ 0) GaN films grown on (1 $\bar{1}$ 02) sapphire substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1658-1661		27
143	Dislocation filtering and polarity in the selective area growth of GaN nanowires by continuous-flow metal organic vapor phase epitaxy. <i>Applied Physics Express</i> , 2016 , 9, 015502	2.4	26
142	Phase separation in metalorganic vapor-phase epitaxy Al _x Ga _(1-x) N films deposited on 6H-SiC. <i>Applied Physics Letters</i> , 2000 , 77, 4310-4312	3.4	26
141	Polar and semipolar GaN/Al _{0.5} Ga _{0.5} N nanostructures for UV light emitters. <i>Semiconductor Science and Technology</i> , 2014 , 29, 084001	1.8	25
140	Optimization of Si/N Treatment Time of Sapphire Surface and Its Effect on the MOVPE GaN Overlayers. <i>Physica Status Solidi A</i> , 1999 , 176, 677-681		25
139	Evolution and prevention of meltback etching: Case study of semipolar GaN growth on patterned silicon substrates. <i>Journal of Applied Physics</i> , 2017 , 122, 105108	2.5	24
138	Epitaxial orientation of III-nitrides grown on R-plane sapphire by metal-organic-vapor-phase epitaxy. <i>Applied Physics Letters</i> , 2006 , 89, 111915	3.4	24
137	Correlation between threading dislocation density and the refractive index of AlN grown by molecular-beam epitaxy on Si(111). <i>Applied Physics Letters</i> , 2003 , 82, 1386-1388	3.4	24
136	Characterization of High-k Ta ₂ Si Oxidized Films on 4H-SiC and Si Substrates as Gate Insulator. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G259	3.9	24
135	Submicron periodic poling and chemical patterning of GaN. <i>Applied Physics Letters</i> , 2005 , 87, 062106	3.4	24
134	High-quality distributed Bragg reflectors based on Al _x Ga _(1-x) N/GaN multilayers grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2001 , 79, 2136-2138	3.4	24
133	Evidence of multimicrometric coherent δ -precipitates in a hot-forged δ -nickel-based superalloy. <i>Journal of Microscopy</i> , 2016 , 263, 106-12	1.9	23

132	Comparative study of GaN layers grown on insulating AlN and conductive AlGaIn buffer layers. <i>Semiconductor Science and Technology</i> , 1999 , 14, L33-L36	1.8	23
131	Growth of semipolar (202 1) GaN layers on patterned silicon (114) 1 \times off by Metal Organic Vapor Phase Epitaxy. <i>Journal of Crystal Growth</i> , 2015 , 419, 88-93	1.6	22
130	Transmission electron microscopy investigation of microtwins and double positioning domains in (111) 3C-SiC in relation with the carbonization conditions. <i>Applied Physics Letters</i> , 2009 , 95, 081903	3.4	22
129	In situ growth monitoring of distributed GaN/AlGaIn Bragg reflectors by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2002 , 80, 174-176	3.4	22
128	Hexagonal c-axis GaN layers grown by metalorganic vapor-phase epitaxy on Si(001). <i>Journal of Crystal Growth</i> , 2005 , 280, 44-53	1.6	21
127	GaN/Al _{0.5} Ga _{0.5} N (11-22) semipolar nanostructures: A way to get high luminescence efficiency in the near ultraviolet range. <i>Journal of Applied Physics</i> , 2011 , 110, 084318	2.5	20
126	Strain engineering in GaN layers grown on silicon by molecular beam epitaxy: The critical role of growth temperature. <i>Journal of Crystal Growth</i> , 2009 , 311, 2002-2005	1.6	20
125	On the origin of basal stacking faults in nonpolar wurtzite films epitaxially grown on sapphire substrates. <i>Journal of Applied Physics</i> , 2012 , 112, 113518	2.5	20
124	Electron energy-loss spectroscopy characterization of pyramidal defects in metalorganic vapor-phase epitaxy Mg-doped GaN thin films. <i>Applied Physics Letters</i> , 2000 , 77, 2115-2117	3.4	20
123	AlGaIn/GaN/AlGaIn DH-HEMTs grown by MBE on Si(1 1 1). <i>Journal of Crystal Growth</i> , 2005 , 278, 393-396	1.6	19
122	Fiber-draw-induced elongation and break-up of particles inside the core of a silica-based optical fiber. <i>Journal of the American Ceramic Society</i> , 2017 , 100, 1814-1819	3.8	18
121	Use of thulium-doped LaF ₃ nanoparticles to lower the phonon energy of the thulium's environment in silica-based optical fibres. <i>Optical Materials</i> , 2017 , 68, 24-28	3.3	18
120	Impact of sapphire nitridation on formation of Al-polar inversion domains in N-polar AlN epitaxial layers. <i>Journal of Applied Physics</i> , 2017 , 122, 155303	2.5	18
119	Nature and origin of V-defects present in metalorganic vapor phase epitaxy-grown (In _x Al _{1-x})N layers as a function of InN content, layer thickness and growth parameters. <i>Journal of Crystal Growth</i> , 2012 , 353, 108-114	1.6	17
118	Ductile relaxation in cracked metal-organic chemical-vapor-deposition-grown AlGaIn films on GaN. <i>Journal of Applied Physics</i> , 2005 , 97, 123504	2.5	17
117	Three-dimensionally nucleated growth of gallium nitride by low-pressure metalorganic vapour phase epitaxy. <i>Journal of Crystal Growth</i> , 2003 , 258, 232-250	1.6	17
116	Substrate free GaAs photovoltaic cells on Pd-coated silicon with a 20% AM1.5 efficiency. <i>IEEE Transactions on Electron Devices</i> , 1996 , 43, 1806-1811	2.9	17
115	Intentional polarity conversion of AlN epitaxial layers by oxygen. <i>Scientific Reports</i> , 2018 , 8, 14111	4.9	17

114	Proposition of a model elucidating the AlN-on-Si (111) microstructure. <i>Journal of Applied Physics</i> , 2018 , 123, 215701	2.5	16
113	MBE-grown high-quality (Al,Ga)N/GaN distributed Bragg reflectors for resonant cavity LEDs. <i>Semiconductor Science and Technology</i> , 2001 , 16, 913-917	1.8	16
112	Study of defect management in the growth of semipolar (11-22) GaN on patterned sapphire. <i>Journal Physics D: Applied Physics</i> , 2015 , 48, 325103	3	14
111	Phase separation in GaN/AlGaIn quantum dots. <i>Applied Physics Letters</i> , 2009 , 95, 141901	3.4	14
110	Lattice relaxation and three-dimensional reflection high-energy electron-diffraction analysis of strained epitaxial Co/Mn superlattices. <i>Journal of Applied Physics</i> , 1994 , 76, 2817-2824	2.5	14
109	Defect blocking via laterally induced growth of semipolar (1 0 1 -1) GaN on patterned substrates. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 475104	3	13
108	Metal Organic Vapor Phase Epitaxy of Monolithic Two-Color Light-Emitting Diodes Using an InGaIn-Based Light Converter. <i>Applied Physics Express</i> , 2013 , 6, 092105	2.4	13
107	AlGaIn-Based Light Emitting Diodes Using Self-Assembled GaN Quantum Dots for Ultraviolet Emission. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JG01	1.4	13
106	Heteroepitaxial growth of BeSe on vicinal Si(001) surfaces. <i>Applied Physics Letters</i> , 1998 , 73, 957-959	3.4	13
105	Correlation between the structural and transport properties of granular CoAg systems prepared by MBE. <i>Journal of Magnetism and Magnetic Materials</i> , 1995 , 148, 313-314	2.8	13
104	The ternary system holmium-boron-carbon; isothermal section at 1500 °C. <i>Journal of the Less Common Metals</i> , 1985 , 110, 295-298		13
103	Direct insight into grains formation in Si layers grown on 3C-SiC by chemical vapor deposition. <i>Acta Materialia</i> , 2015 , 98, 336-342	8.4	12
102	Influence of 3C-SiC/Si (111) template properties on the strain relaxation in thick GaN films. <i>Journal of Crystal Growth</i> , 2014 , 398, 23-32	1.6	12
101	Epitaxial Lateral Overgrowth of GaN on Silicon (111). <i>Physica Status Solidi A</i> , 2001 , 188, 733-737		12
100	Successive selective growth of semipolar (11-22) GaN on patterned sapphire substrate. <i>Semiconductor Science and Technology</i> , 2015 , 30, 065001	1.8	11
99	Influence of the heterostructure design on the optical properties of GaN and Al _{0.1} Ga _{0.9} N quantum dots for ultraviolet emission. <i>Journal of Applied Physics</i> , 2017 , 122, 085706	2.5	11
98	In-Plane Polarities of Nonpolar Wurtzite Epitaxial Films Deposited on m- and r-plane Sapphire Substrates. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 090211	1.4	11
97	Study of the growth mechanisms of GaN/(Al, Ga)N quantum dots: Correlation between structural and optical properties. <i>Journal of Applied Physics</i> , 2011 , 109, 053514	2.5	11

96	Filtering of Defects in Semipolar (11-22) GaN Using 2-Steps Lateral Epitaxial Overgrowth. <i>Nanoscale Research Letters</i> , 2010 , 5, 1878-81	5	11
95	AlGa _N /Ga _N HEMTs grown on silicon (001) substrates by molecular beam epitaxy. <i>Superlattices and Microstructures</i> , 2006 , 40, 295-299	2.8	11
94	Molecular beam epitaxy of quantum well structures. <i>Journal of Crystal Growth</i> , 1996 , 160, 211-219	1.6	11
93	Investigation of Al _{0.5} Ga _{0.5} N quantum dot properties for the design of ultraviolet emitters. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FG06	1.4	11
92	Demonstration of Electrically Injected Semipolar Laser Diodes Grown on Low-Cost and Scalable Sapphire Substrates. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 47106-47111	9.5	11
91	Internal quantum efficiencies of AlGa _N quantum dots grown by molecular beam epitaxy and emitting in the UVA to UVC ranges. <i>Journal of Applied Physics</i> , 2019 , 126, 205701	2.5	11
90	AlGa _N /Ga _N HEMTs with an InGa _N back-barrier grown by ammonia-assisted molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 480-483	1.6	10
89	Anisotropic chemical etching of semipolar [1011]/[101+1] ZnO crystallographic planes: polarity versus dangling bonds. <i>Nanotechnology</i> , 2009 , 20, 065701	3.4	10
88	Investigation of AlN films grown by molecular beam epitaxy on vicinal Si(111) as templates for GaN quantum dots. <i>Applied Physics Letters</i> , 2006 , 89, 231903	3.4	10
87	Growth of wurtzite-GaN on silicon (100) substrate by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2187-2190		10
86	γ precipitates with a twin orientation relationship to their hosting grain in a γ nickel-based superalloy. <i>Scripta Materialia</i> , 2018 , 153, 10-13	5.6	9
85	Properties of AlN layers grown on c-sapphire substrate using ammonia assisted MBE. <i>Journal of Crystal Growth</i> , 2018 , 499, 40-46	1.6	9
84	Growth optimization and characterization of lattice-matched Al _{0.82} In _{0.18} N optical confinement layer for edge emitting nitride laser diodes. <i>Journal of Crystal Growth</i> , 2012 , 338, 20-29	1.6	9
83	Blue Light-Emitting Diodes Grown on ZnO Substrates. <i>Applied Physics Express</i> , 2013 , 6, 042101	2.4	9
82	Study of (Al,Ga)N Bragg Mirrors Grown on Al ₂ O ₃ (0001) and Si(111) by Metalorganic Vapor Phase Epitaxy. <i>Physica Status Solidi A</i> , 2001 , 188, 899-903		9
81	Effect of the nucleation layer deposition temperature on the nature of defects in GSMBE GaN films. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 423-428	1.6	9
80	On the morphologies of oxides particles in optical fibers: Effect of the drawing tension and composition. <i>Optical Materials</i> , 2019 , 87, 74-79	3.3	8
79	Ferromagnetic resonance determination of fcc-hcp structural change in epitaxial Co/Mn superlattices. <i>Journal of Applied Physics</i> , 1994 , 75, 5601-5603	2.5	8

78	Growth of Ga- and N-polar GaN layers on O face ZnO substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2014 , 388, 35-41	1.6	7
77	Capping green emitting (Ga,In)N quantum wells with (Al,Ga)N: impact on structural and optical properties. <i>Semiconductor Science and Technology</i> , 2014 , 29, 035016	1.8	7
76	Microstructural studies of GaN grown on (0001) sapphire by MOVPE. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 43, 274-278	3.1	7
75	Selective heteroepitaxy on deeply grooved substrate: A route to low cost semipolar GaN platforms of bulk quality. <i>Applied Physics Letters</i> , 2016 , 109, 082101	3.4	7
74	GaN films and GaN/AlGaIn quantum wells grown by plasma assisted molecular beam epitaxy using a high density radical source. <i>Journal of Crystal Growth</i> , 2016 , 433, 165-171	1.6	6
73	Strain- and surface-induced modification of photoluminescence from self-assembled GaN/Al _{0.5} Ga _{0.5} N quantum dots: strong effect of capping layer and atmospheric condition. <i>Nanotechnology</i> , 2014 , 25, 305703	3.4	6
72	Fabrication and growth of GaN-based micro and nanostructures. <i>International Journal of Nanotechnology</i> , 2012 , 9, 412	1.5	6
71	Plasmon energy from strained GaN quantum wells. <i>Applied Physics Letters</i> , 2013 , 103, 021901	3.4	6
70	Green emission from semipolar InGaIn quantum wells grown on low-defect (0001) GaN templates fabricated on patterned r-sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 105-111	1.3	6
69	Semipolar (10-11) GaN growth on silicon-on-insulator substrates: Defect reduction and meltback etching suppression. <i>Journal of Applied Physics</i> , 2019 , 125, 035703	2.5	6
68	Correlative investigation of Mg doping in GaN layers grown at different temperatures by atom probe tomography and off-axis electron holography. <i>Nanotechnology</i> , 2020 , 31, 045702	3.4	6
67	Silicon Growth on 3C-SiC(001)/Si(001): Pressure Influence and Thermal Effect. <i>Materials Science Forum</i> , 2015 , 821-823, 978-981	0.4	5
66	Microstructural study of pseudomorphic ZnSe films grown on bare GaAs substrates. <i>Journal of Crystal Growth</i> , 1997 , 182, 45-52	1.6	5
65	Ta ₂ Si Thermal Oxidation: A Simple Route to a High-k Gate Dielectric on 4H-SiC. <i>Electrochemical and Solid-State Letters</i> , 2004 , 7, F93		5
64	Realization of waveguiding epitaxial GaN layers on Si by low-pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2003 , 83, 5139-5141	3.4	5
63	Molecular beam epitaxy of Zn _x Be _{1-x} Se: Influence of the substrate nature and epilayer properties. <i>Journal of Electronic Materials</i> , 2000 , 29, 883-886	1.9	5
62	Sub-bandgap optical absorption of MOVPE-GaN grown under controlled nucleation.. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 59, 24-28	3.1	5
61	Investigations by high-resolution X-ray diffraction (HRXRD) and transmission electron microscopy (TEM) of (BeTe/ZnSe) superlattices grown by molecular beam epitaxy onto GaAs buffer epilayer. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 498-501	1.6	5

60	Molecular-beam epitaxy of Zn _x Be _{1-x} Se layers on vicinal Si(0 0 1) substrates. <i>Journal of Crystal Growth</i> , 1999 , 201-202, 514-517	1.6	5
59	Crystalline magnesium nitride (Mg ₃ N ₂): From epitaxial growth to fundamental physical properties. <i>Physical Review Materials</i> , 2020 , 4,	3.2	5
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